

P-Channel Mosfet

Features

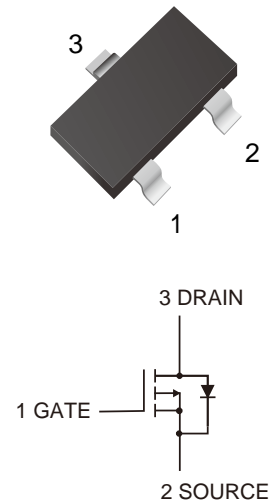
- $V_{DS} = -30V$, $I_D = -4.2A$
- $R_{DS(on)} < 70m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(on)} < 80m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(on)} < 120m\Omega$ ($V_{GS} = -2.5V$)
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package
- Lead free in comply with EU RoHS 2011/65/EU directives

Mechanical Data

- Case: SOT-23
- Approx. Weight: 8.1mg

Ordering Information

Part Number	Marking	Shipping	Reel
LTM3401PA-TR3	A1	3000PCS Tape&Reel	7 inches
LTM3401PA-TR12	A1	12000PCS Tape&Reel	13 inches



Maximum Ratings ($T_a = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DSS}	Drain - source Voltage	-30	V
V_{GSS}	Gate - source - Voltage	± 12	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	-4.2
		$T_C = 100^\circ C$	-2.7
I_{DM}	Pulsed Drain Current (note 1)	-17	A
P_D	Power Dissipation	1.2	W
T_J, T_{STG}	Operating And Storage Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	104	$^\circ C/W$

Thermal Characteristics ($T_a=25$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
I_{GSS}	Gate -body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 10V$			± 100	nA
$V_{GS(th)}$	Gate-Threshold Voltage (note 2)	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7	-1	-1.3	V
$R_{DS(on)}$	Drain-source On-Resistance(note 2)	$V_{GS}=-10V, I_D=-4.2A$ $V_{GS}=-4.5V, I_D=-4A$ $V_{GS}=-2.5V, I_D=-1A$		48 56 72	70 80 120	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-4.2A$		10		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS}=-15V$		880		pF
C_{oss}	Output Capacitance	$V_{GS}=0V$		105		
C_{rss}	Reverse Transfer Capacitance	$f=1MHz$		65		
Q_g	Total Gate Charge	$V_{DS}=-15V$		8.5		nC
Q_{GS}	Gate-Source Charge	$I_D=-4.2A$		1.8		
Q_{gd}	Gate-Drain("Miller") Charge	$V_{GS}=-4.5V$		2.7		

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, I_D=-4.2A,$ $V_{GS}=-10V, R_{GEN}=6\Omega$		7		ns
t_r	Turn-on Rise Time			3		
$t_{d(off)}$	Turn-off Delay Time			30		
t_f	Turn-off Fall Time			12		

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current			-4.2	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-17	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-4.2A,$		-1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=-4.2A,$ $di/dt=100A/\mu s$		11	ns
Q_{rr}	Reverse Recovery Charge			3.5	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.



Characteristic Curves

Fig.1 On-Region Characteristics

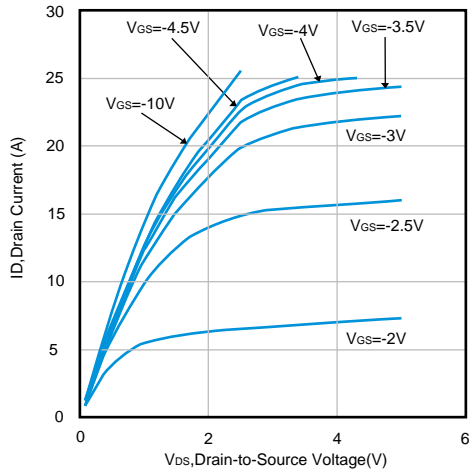


Fig.2 Transfer Characteristics

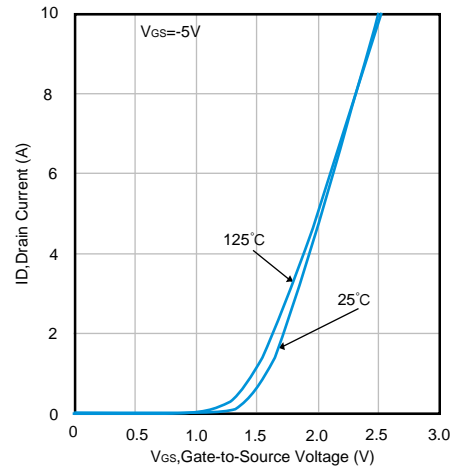


Fig.3 RDS(on) (Ω) vs ID

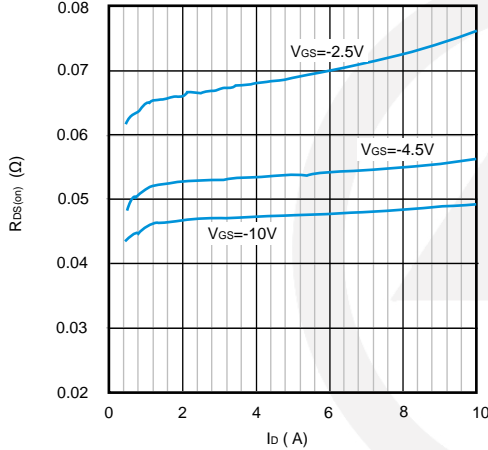


Fig.4 Temperature vs Gate Threshold Voltage

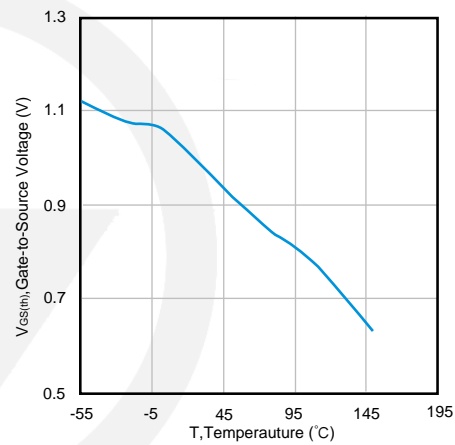


Fig.5 RDS(on) vs VGS

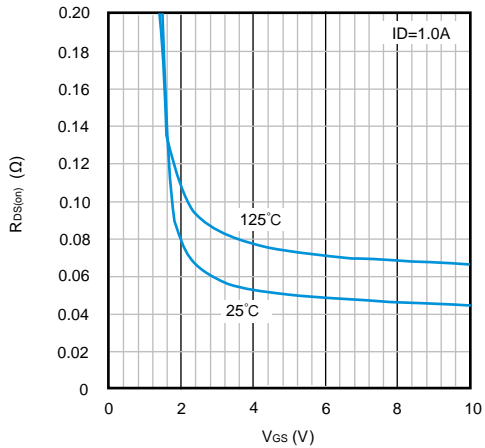
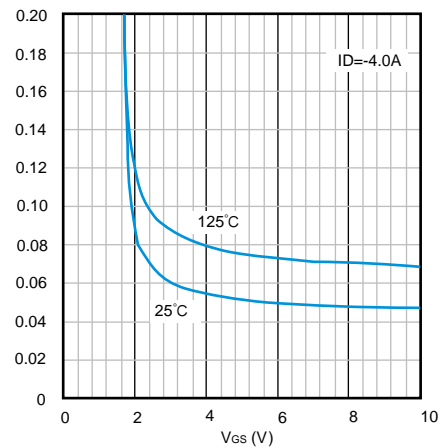
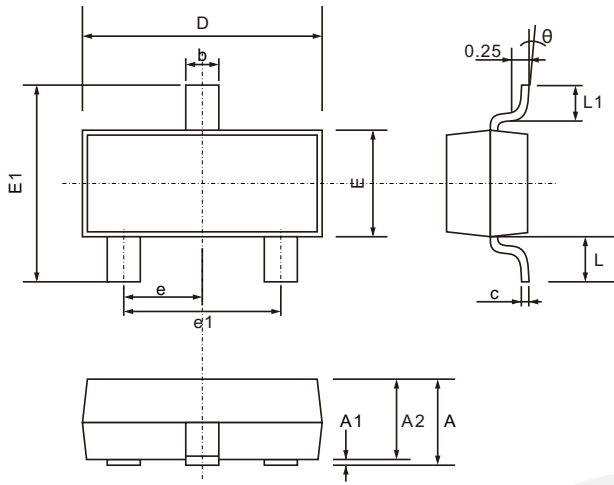


Fig.5 RDS(on) vs VGS



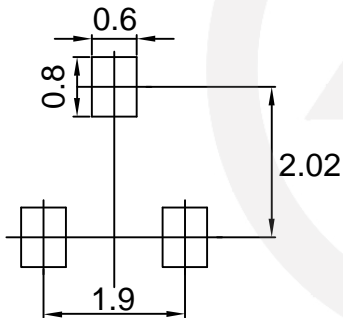
SOT-23 Package Outline

Unit: mm



SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.200
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.200
D	2.700	3.100
E	1.200	1.400
E1	2.200	2.600
e	0.950 TYP.	
e1	1.750	2.050
L	0.550 TYP.	
L1	0.300	0.500
θ	0°	8°

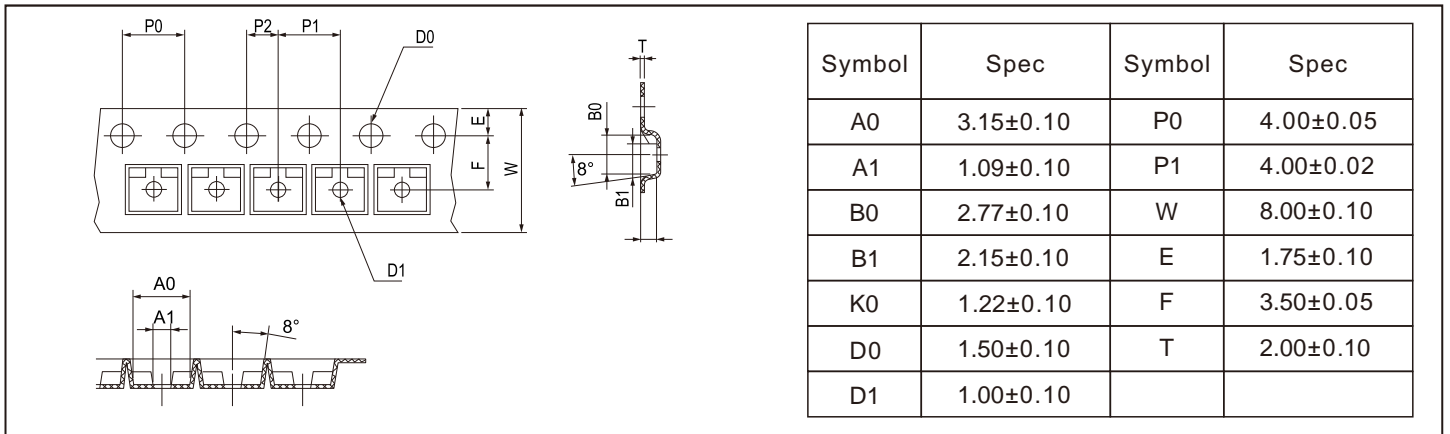
SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$
 3. The pad layout is for reference purpose only.

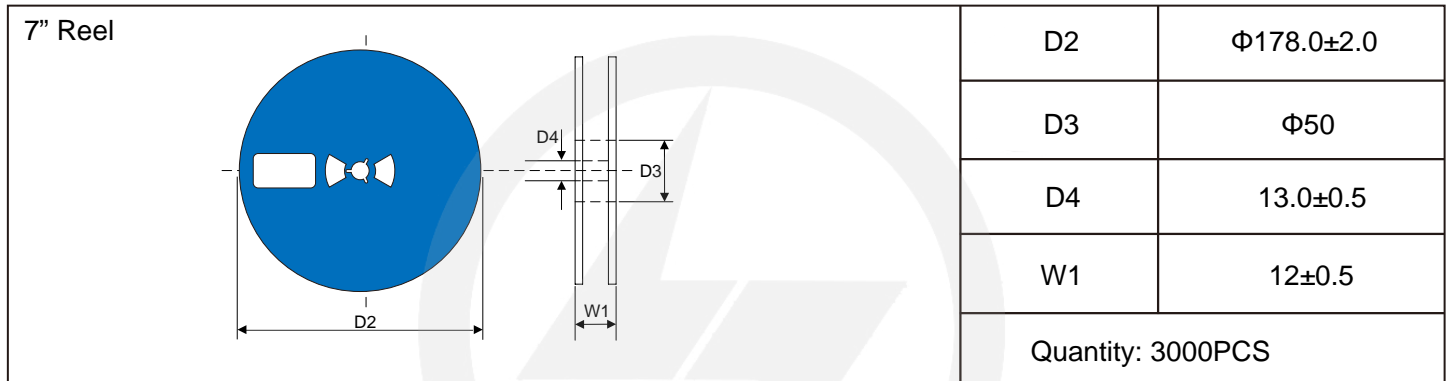
Carrier Tape Dimensions

Unit : mm



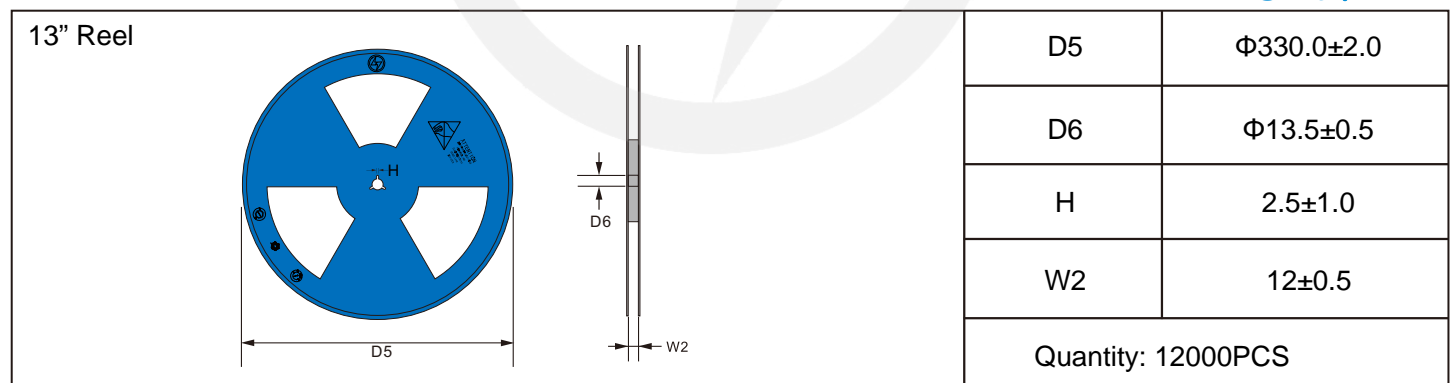
Reel Dimensions

Unit : mm

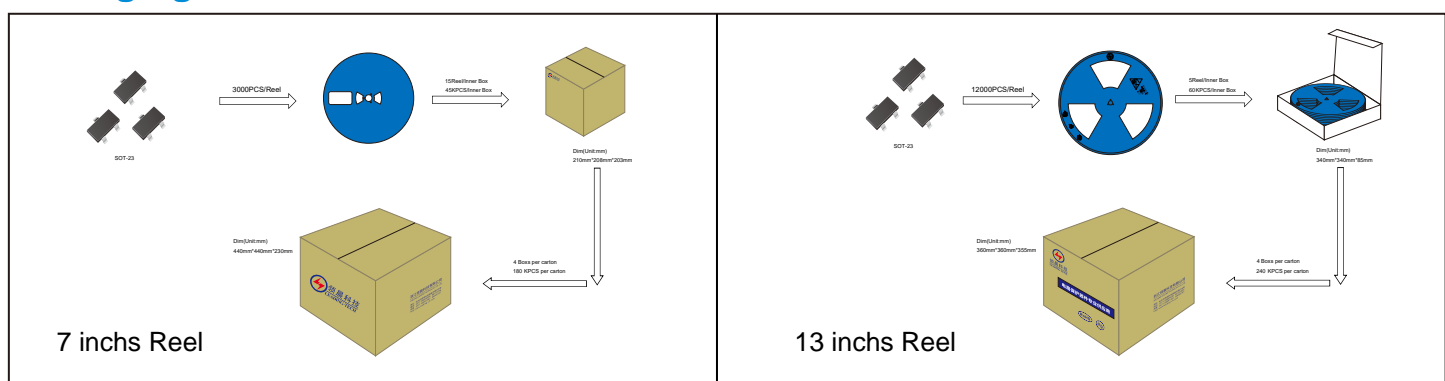


Reel Dimensions

Unit : mm



Packaging





Recommended Soldering Conditions



Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	3°C/second max.
Preheat	
-Temperature Min (T _{S min})	150°C
-Temperature Max (T _{S max})	200°C
-Time (min to max) (t _s)	60-180 seconds
T _{S max} to T _L	
-Ramp-up Rate	3°C/second max.
Time maintained above:	
-Temperature (T _L)	217°C
-Time (t _L)	60-150 seconds
Peak Temperature (T _P)	260°C
Time within 5°C of actual Peak Temperature (t _p)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

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Version Update Information

Series NO.	Enactment/Revision Date	Effective Date	Version	Revision Content	Revision Reason	Revision Person	Note
01	2024.10.17	2024.10.17	3.0	New file	/	Ding	
02	2026.03.05	2026.03.05	3.1	Package outline E1(max)=2.6mm	/	Ding	